

本博士論文は、以下の出版論文をもとにしている：

- 第3章：H. Amekura, N. Kishimoto and T. Saito, *Photoconductivity evolution due to carrier trapping by defects in 17 MeV-proton irradiated silicon*, J. Appl. Phys. **77**, pp.4984-4992 (1995).
- 第4章：H. Amekura, N. Kishimoto and K. Kono, *Particle-induced conductivity and photoconductivity of silicon under 17 MeV proton irradiation*, J. Appl. Phys. **84**, pp.4834-4841 (1998).
- 第5章：H. Amekura, N. Kishimoto and K. Kono, *Simultaneous irradiation of photons and high-energy protons to Si: in-situ photo-detection in strong radiation fields*, J. Appl. Phys., 投稿予定.
- 第6章：H. Amekura, N. Kishimoto and K. Kono, *Radiation-induced two-step degradation of Si photoconductors and space solar cells*. IEEE Trans. Nuclear Science, **45**, pp.1508-1513, (1998).
- 第7章：N. Kishimoto, H. Amekura, K. Kono and T. Saito, *Particle-induced and photo-conductivities in amorphous Si:H under proton irradiation*, Mat. Res. Soc. Symp. Proc., **439**, pp.679-684 (1997).
- 第8章：H. Amekura, N. Kishimoto and K. Kono, *Persistent excited conductivity induced by proton irradiation in a-Si:H*, Mat. Sci. Forum, **258-263**, pp.599-604 (1997).

また関連する著者の出版物としては、以上6件の他、

7. H. Amekura, N. Kishimoto, K. Kono and T. Saito
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 11. K. Kono, N. Kishimoto, H. Amekura and T. Saito
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 12. N. Kishimoto, H. Amekura, K.Kono and C.G.Lee
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 13. N. Kishimoto, H. Amekura, K. Kono and C.G. Lee
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 18. N. Kishimoto and H. Amekura
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Negative copper ion implantation into silica glasses at high dose rates and the optical measurements. Nucl. Instr. & Meth. in Phys. Res., B 127/128, pp.579-582 (1997).
21. N. Kishimoto, V.T.Gritsyna, K.Kono, H. Amekura and T. Saito
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26. S. Wang, H. Amekura, A. Eckau, R. Carius and Ch. Buchal
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27. K. Kono, H. Amekura and N. Kishimoto
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28. Thi Thi Lay, H. Amekura, Y.Takeda and N.Kishimoto,
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また出版物ではないが、関連する成果として、

特許登録

29. N. Kishimoto and H. Amekura

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No. 2535786, Japan (1996).

30. N. Kishimoto and H. Amekura

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受賞

31. H. Amekura

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